

# 1SS165

## Silicon Schottky Barrier Diode for CATV Balanced Mixer

# HITACHI

Rev. 0  
Oct. 1995

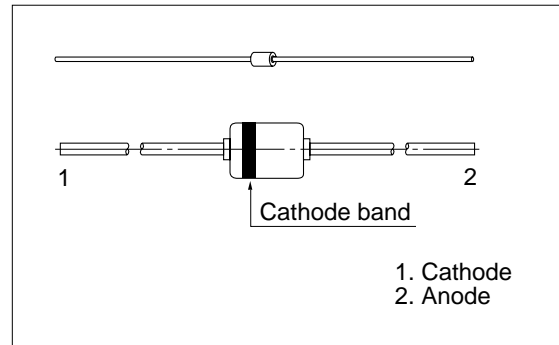
### Features

- Low capacitance.(C=1.0pF max)
- Small glass package (MHD) enables easy mounting and high reliability.

### Ordering Information

TType No.	Cathode band	Package Code
1SS165	Green	MHD

### Outline



### Absolute Maximum Ratings (Ta = 25°C)

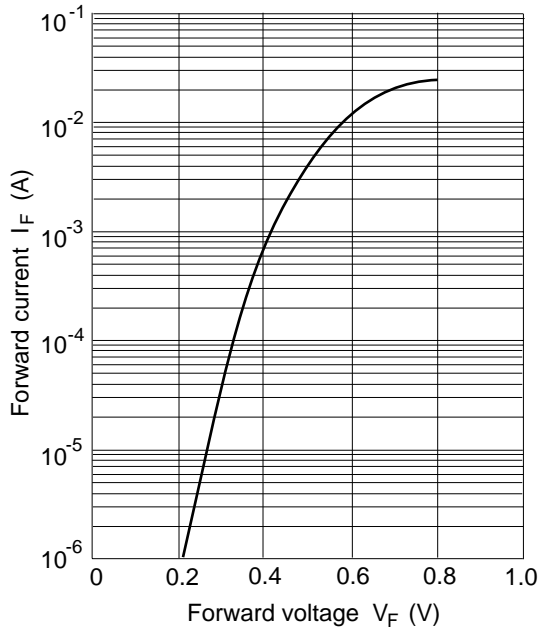
Item	Symbol	Value	Unit
Reverse voltage	$V_R$	10	V
Average forward current	$I_o$	15	mA
Peak forward current	$I_{FM}$	35	mA
Power dissipation	$P_d$	150	mW
Junction temperature	$T_j$	100	°C
Storage temperature	$T_{stg}$	-55 to +100	°C

### Electrical Characteristics (Ta = 25°C)

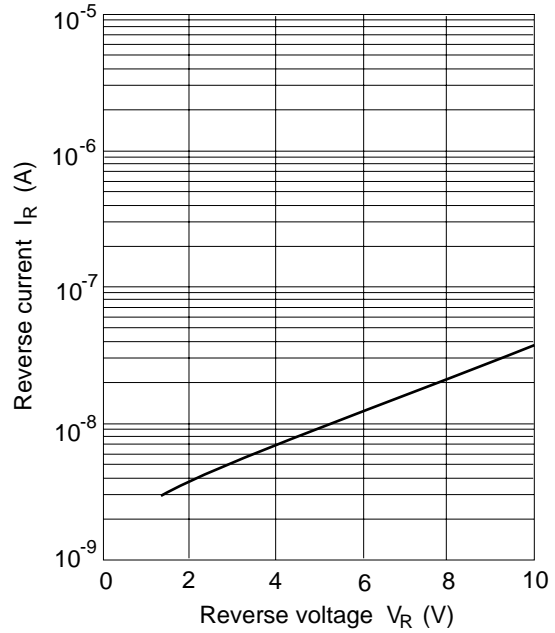
Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	$V_{F1}$	365	—	435	mV	$I_F = 1 \text{ mA}$
	$V_{F2}$	520	—	600		$I_F = 10 \text{ mA}$
Reverse current	$I_{R1}$	—	—	0.2	$\mu\text{A}$	$V_R = 2 \text{ V}$
	$I_{R2}$	—	—	10		$V_R = 10 \text{ V}$
Capacitance	C	—	—	1.0	pF	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$
Capacitance deviation	$\Delta C$	—	—	0.1	pF	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$
Forward voltage deviation	$\Delta V_{F1}$	—	—	10	mV	$I_F = 2.5 \text{ mA}$
	$\Delta V_{F2}$	—	—	10		$I_F = 10 \text{ mA}$
ESD-Capability	—	30	—	—	V	*C=200pF, Both forward and reverse direction 1 pulse.

\* Failure criterion ;  $I_R \geq 50\mu\text{A}$

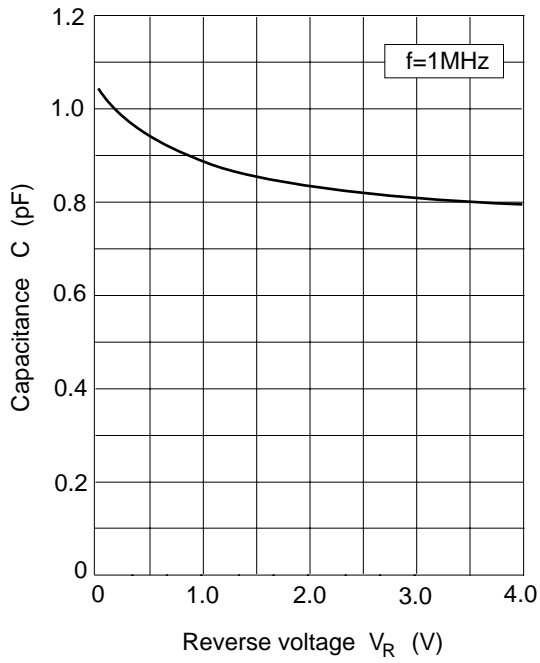
\*\* Each group shall unify a multiple of 4 diodes



**Fig.1 Forward current Vs. Forward voltage**



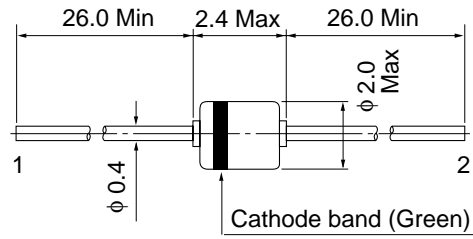
**Fig.2 Reverse current Vs. Reverse voltage**



**Fig.3 Capacitance Vs. Reverse voltage**

### Package Dimensions

Unit: mm



1 Cathode  
2 Anode

HITACHI Code	MHD
JEDEC Code	DO-34
EIAJ Code	—
Weight (g)	0.084